

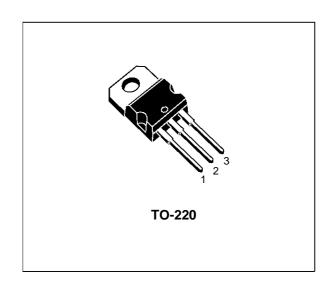
TIP41A/41B/41C TIP42A/42B/42C

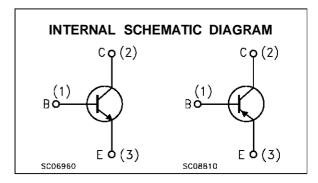
COMPLEMENTARY SILICON POWER TRANSISTORS

SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP41A, TIP41B and TIP41C are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intented for use in medium power linear and switching applications. The complementary PNP types are TIP42A, TIP42B and TIP42C.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value			Unit
	NPN		TIP41A	TIP41B	TIP41C	
		PNP	TIP42A	TIP42B	TIP42C	
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	80	100	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)		5			V
Ic	Collector Current		6			Α
I _{CM}	Collector Peak Current		10			Α
Ι _Β	Base Current		3			Α
P_{tot}	Total Dissipation at T _{case} ≤ 25 °C		65		W	
	T _{amb} ≤ 25 °C			2		W
T_{stg}	Storage Temperature	-65 to 150		°C		
Tj	Max. Operating Junction Temperature		°C			

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TIP41A/TIP41B/TIP41C/TIP42A/TIP42B/TIP42C

THERMAL DATA

R _{thj-case}	Thermal Resistance	ce Junction-case	Max	1.92	°C/W
$R_{thj-amb}$	Thermal Resistant	ce Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ °C unless otherwise specified)

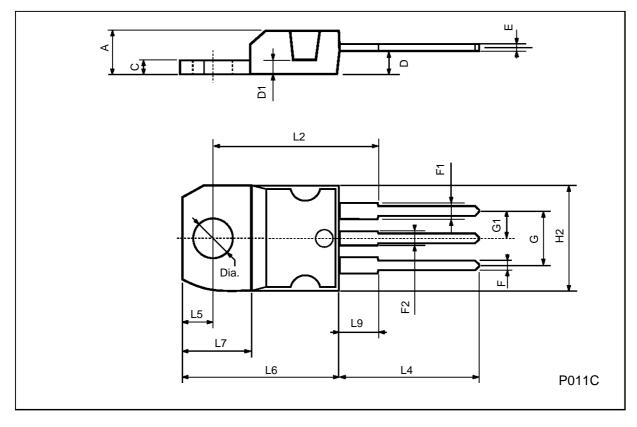
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _B = 0)	for TIP41 A/42A V _{CE} = 30 V for TIP41 B/41 C/42B/42C V _{CB} = 60 V			0.7	mA mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP41A/42A	80 V		0.4 0.4 0.4	mA mA mA
I _{EBO}	Emitter Cut-off Current (Ic = 0)	V _{EB} = 5 V			1	mΑ
VCEO(sus)*	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP41A/42A for TIP41B/42B for TIP41C/42C	60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{C} = 6 \text{ A}$ $I_{B} = 0.$	6 A		1.5	V
V _{BE(on)} *	Base-Emitter Voltage	$I_C = 6 A$ $V_{CE} =$	4 V		2	V
h _{FE} *	DC Current Gain	I _C = 0.3 A			75	
h _{fe}	Small Signal Current Gain	$\begin{split} I_{C} &= 0.5 \text{ A} & V_{CE} = \\ f &= 1 \text{ KHz} & \\ I_{C} &= 0.5 \text{ A} & V_{CE} = \\ f &= 1 \text{ MHz} & \end{split}$	20			

^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %

For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TIP41A/TIP41B/TIP41C/TIP42A/TIP42B/TIP42C

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